

## 1. General description

Planar passivated AC Thyristor Triac power switch in a TO252 (DPAK) surface mountable plastic package with self-protective capabilities against low and high energy transients. This "series ETN" triac will commute the full RMS current at the maximum rated junction temperature ( $T_{j(max)} = 150\text{ °C}$ ) without the aid of a snubber. It is used in applications where "high junction operating temperature capability" is required.

## 2. Features and benefits

- Clamping structure ensuring safe high over-voltage withstand capability
- High junction operating temperature capability ( $T_{j(max)} = 150\text{ °C}$ )
- High minimum IGT for guaranteed immunity to gate noise
- Full cycle AC conduction
- Over-voltage withstand capability to IEC 61000-4-5
- Pin compatible with standard triacs
- Planar passivated for voltage ruggedness and reliability
- Protective self turn-on capability for high energy transients
- Safe clamping capability for low energy over-voltage transients
- Less sensitive gate for high noise immunity
- Triggering in three quadrants only
- Very high immunity to false turn-on by  $dV/dt$  and IEC 61000-4-4 fast transient
- Package meets UL94V0 flammability requirement
- Package is RoHS compliant

## 3. Applications

- AC pumps and fans
- High power solenoids
- Highly inductive, resistive and safety loads
- Large and small appliances (White Goods)
- Applications subject to high temperature ( $T_{j(max)} = 150\text{ °C}$ )

## 4. Quick reference data

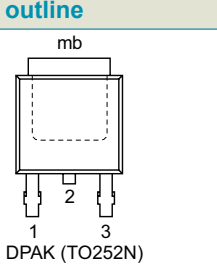

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values	Unit
<b>Absolute maximum rating</b>				
$V_{DRM}$	repetitive peak off-state voltage		800	V
$I_{T(RMS)}$	RMS on-state current	square-wave pulse; $T_{mb} \leq 140\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	2	A
$I_{TSM}$	non-repetitive peak forward current	full sine wave; $t_p = 20\text{ ms}$ ; $T_{j(init)} = 25\text{ °C}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	18	A
		full sine wave; $t_p = 16.7\text{ ms}$ ; $T_{j(init)} = 25\text{ °C}$	19.8	A
$T_j$	junction temperature		150	°C

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+ T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>	-	-	10	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G- T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>	-	-	10	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G- T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>	-	-	10	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 9</a>	-	-	10	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 3 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 10</a>	-	-	2	V
<b>Dynamic characteristics</b>						
dV <sub>D</sub> /dt	rate of rise of off-state voltage	V <sub>DM</sub> = 536 V; T <sub>j</sub> = 125 °C; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; gate open circuit	500	-	-	V/μs
		V <sub>DM</sub> = 536 V; T <sub>j</sub> = 150 °C; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; gate open circuit	200	-	-	V/μs
dI <sub>com</sub> /dt	rate of change of commutating current	V <sub>D</sub> = 400 V; T <sub>j</sub> = 150 °C; I <sub>T(RMS)</sub> = 2 A; dV <sub>com</sub> /dt = 20 V/μs; gate open circuit; snubberless condition	1	-	-	A/ms
		V <sub>D</sub> = 400 V; T <sub>j</sub> = 150 °C; I <sub>T(RMS)</sub> = 2 A; dV <sub>com</sub> /dt = 10 V/μs; gate open circuit	1.5	-	-	A/ms
		V <sub>D</sub> = 400 V; T <sub>j</sub> = 150 °C; I <sub>T(RMS)</sub> = 2 A; dV <sub>com</sub> /dt = 1 V/μs; gate open circuit	3	-	-	A/ms

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	 <p>DPAK (TO252N)</p>	 <p>sym051</p>
2	T2	main terminal 2		
3	G	gate		
mb	T2	mounting base; main terminal 2		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		Version
	Name	Description	
ACTT2S-800ETN	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	TO252N

## 7. Marking

Table 4. Marking codes

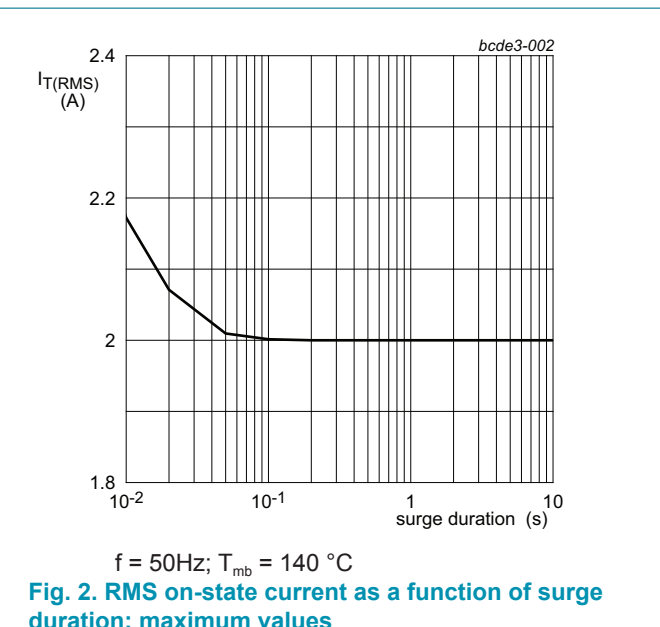
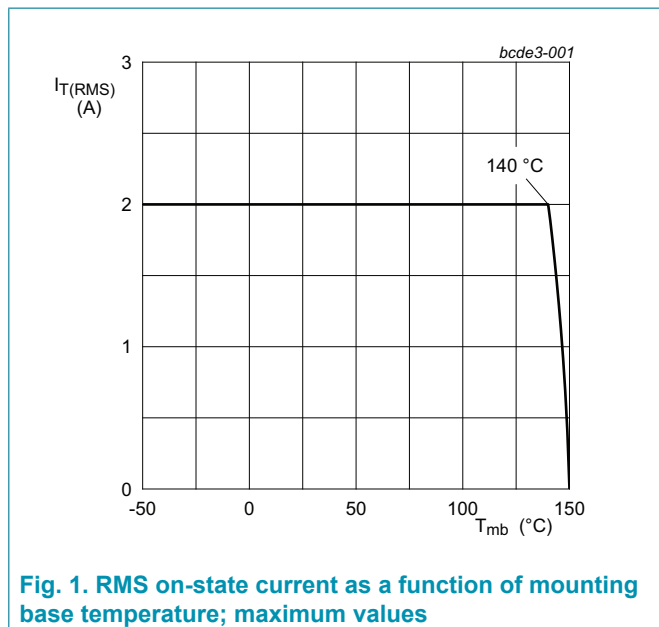
Type number	Marking codes
ACTT2S-800ETN	ACTT2S-800ETN

## 8. Limiting values

**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{DRM}$	repetitive peak off-state voltage		800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 140^{\circ}\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	2	A
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $t_p = 20\text{ ms}$ ; $T_{j(\text{init})} = 25^{\circ}\text{C}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	18	A
		full sine wave; $t_p = 16.7\text{ ms}$ ; $T_{j(\text{init})} = 25^{\circ}\text{C}$	19.8	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ms}$ ; sine wave	1.62	$\text{A}^2/\text{s}$
$dI_T/dt$	rate of rise of on-state current	$I_G = 70\text{mA}$	100	$\text{A}/\mu\text{s}$
$I_{GM}$	peak gate current		2	A
$P_{GM}$	peak gate power		5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	0.5	W
$T_{stg}$	storage temperature		-40 to 150	$^{\circ}\text{C}$
$T_j$	junction temperature		150	$^{\circ}\text{C}$
$V_{pp}$	peak pulse voltage	$T_j = 25^{\circ}\text{C}$ ; non-repetitive, off-state; ten pulses on each voltage polarity; 20s or more between successive pulses	2	kV



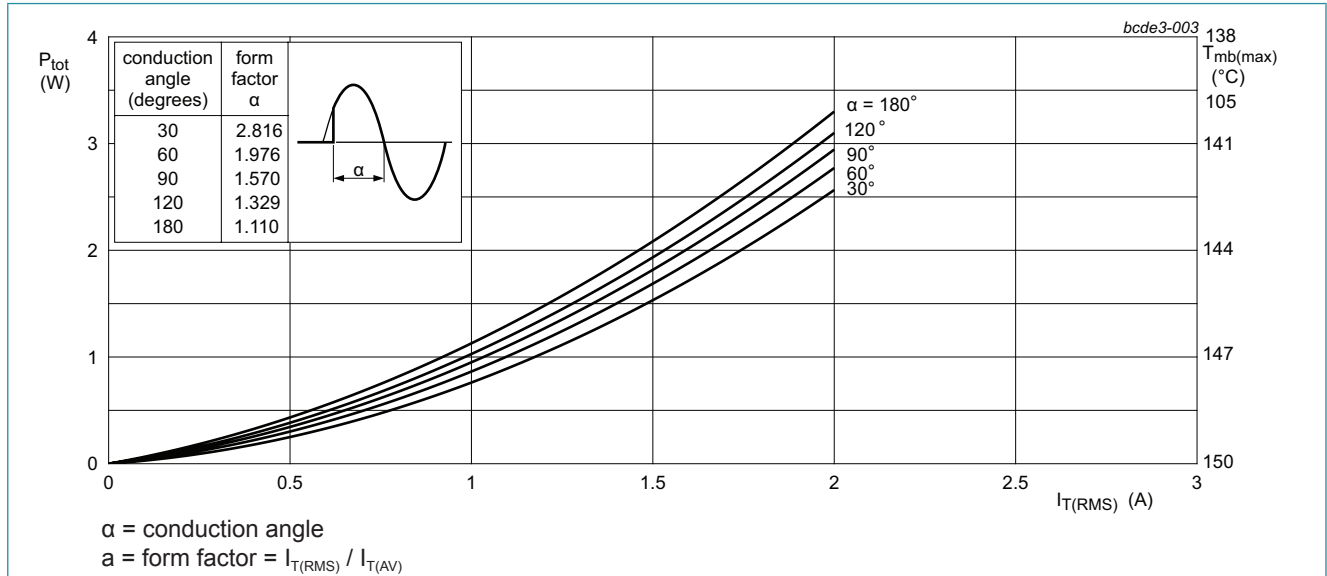


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

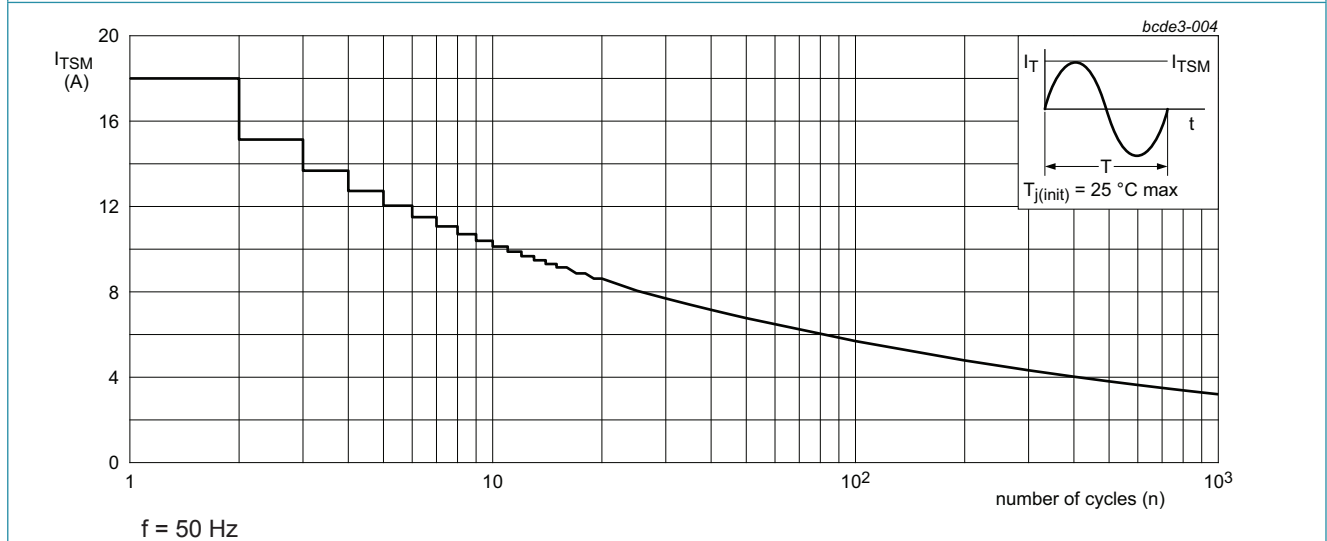


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

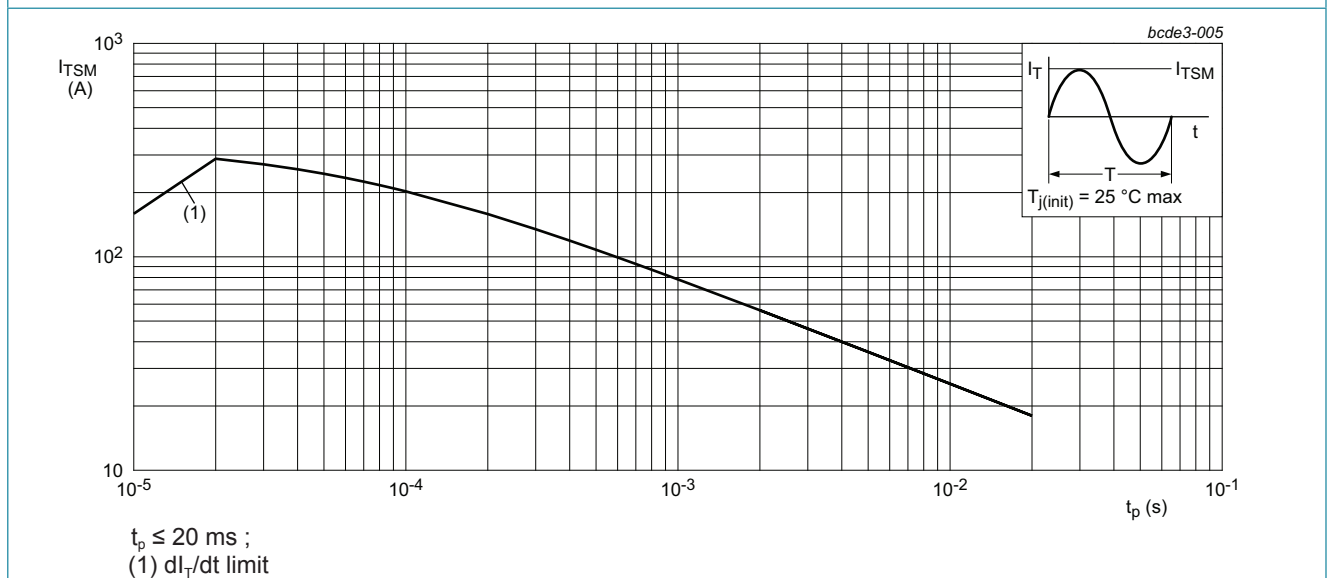


Fig. 5. Total power dissipation as a function of RMS on-state current; maximum values

## 9. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	<a href="#">Fig. 6</a>	-	-	3	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	75	-	K/W

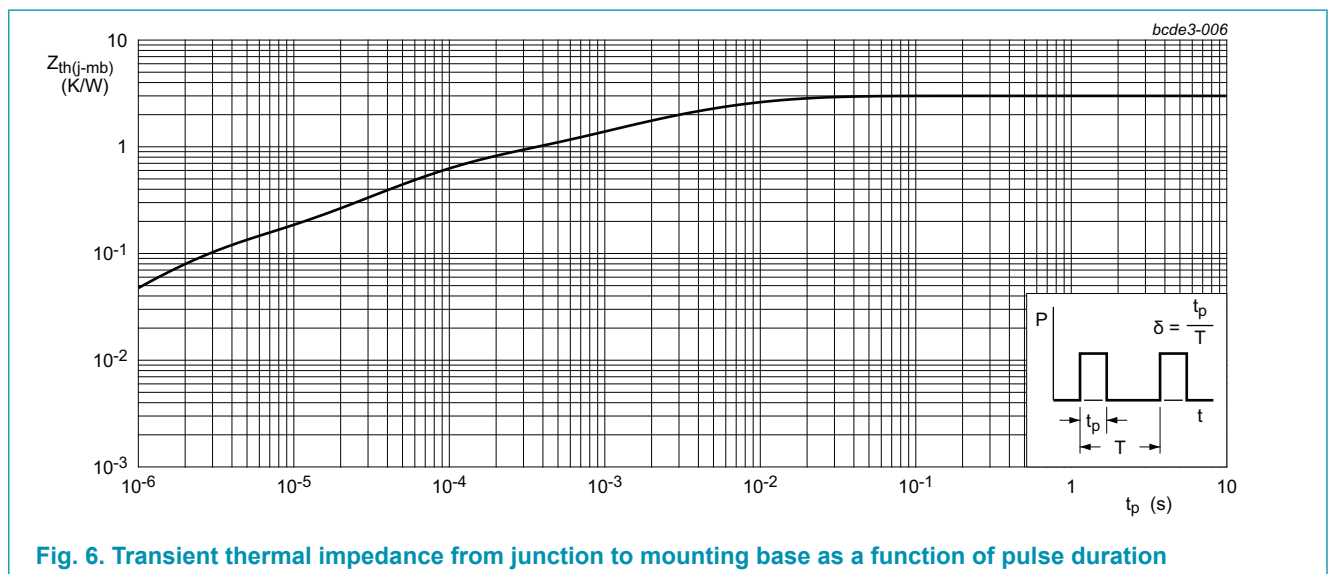
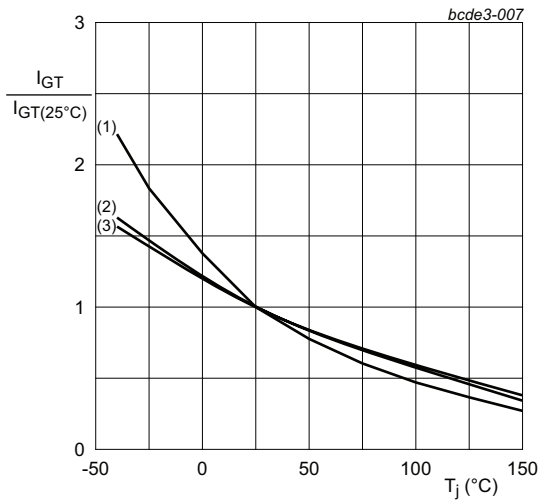


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	-	-	10	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	-	-	10	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	-	-	10	mA
$I_L$	latching current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 8</a>	-	-	25	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 8</a>	-	-	35	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 8</a>	-	-	25	mA
$I_H$	holding current	$V_D = 12\text{ V}$ ; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 9</a>	-	-	10	mA
$V_T$	on-state voltage	$I_T = 3\text{ A}$ ; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 10</a>	-	-	2	V
$V_{GT}$	gate trigger voltage	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 11</a>	-	0.8	1	V
		$V_D = 400\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_J = 150\text{ °C}$ ; <a href="#">Fig. 11</a>	0.2	0.45	-	V
$I_D$	off-state current	$V_D = 800\text{ V}$ ; $T_J = 25\text{ °C}$	-	-	10	$\mu\text{A}$
		$V_D = 800\text{ V}$ ; $T_J = 150\text{ °C}$	-	-	2	mA
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$ ; $T_J = 125\text{ °C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit	500	-	-	V/ $\mu\text{s}$
		$V_{DM} = 536\text{ V}$ ; $T_J = 150\text{ °C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit	200	-	-	V/ $\mu\text{s}$
$dI_{com}/dt$	rate of change of commutating current	$V_D = 400\text{ V}$ ; $T_J = 150\text{ °C}$ ; $I_{T(RMS)} = 2\text{ A}$ ; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$ ; gate open circuit; snubberless condition	1	-	-	A/ms
		$V_D = 400\text{ V}$ ; $T_J = 150\text{ °C}$ ; $I_{T(RMS)} = 2\text{ A}$ ; $dV_{com}/dt = 10\text{ V}/\mu\text{s}$ ; gate open circuit	1.5	-	-	A/ms
		$V_D = 400\text{ V}$ ; $T_J = 150\text{ °C}$ ; $I_{T(RMS)} = 2\text{ A}$ ; $dV_{com}/dt = 10\text{ V}/\mu\text{s}$ ; gate open circuit	3	-	-	A/ms



- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

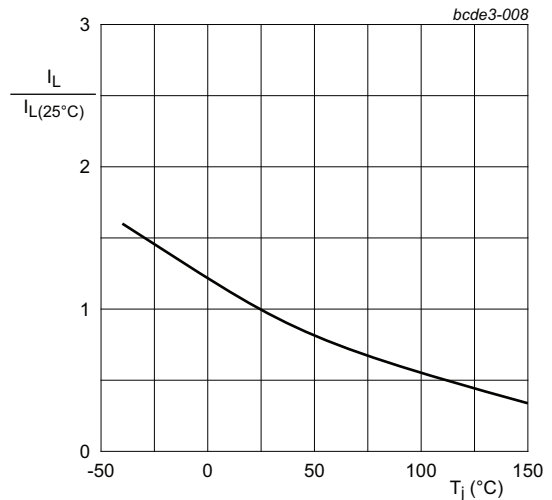


Fig. 8. Normalized latching current as a function of junction temperature

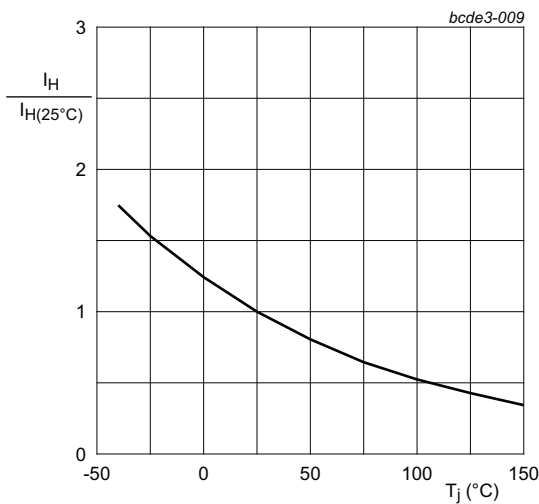
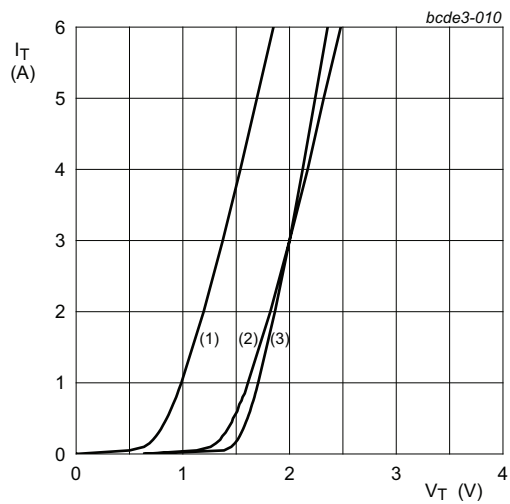


Fig. 9. Normalized holding current as a function of junction temperature



$V_o = 0.673 \text{ V}$ ;  $R_s = 0.5217 \Omega$

- (1)  $T_j = 150^\circ\text{C}$ ; typical values
- (2)  $T_j = 150^\circ\text{C}$ ; maximum values
- (3)  $T_j = 25^\circ\text{C}$ ; maximum values

Fig. 10. On-state current as a function of on-state voltage

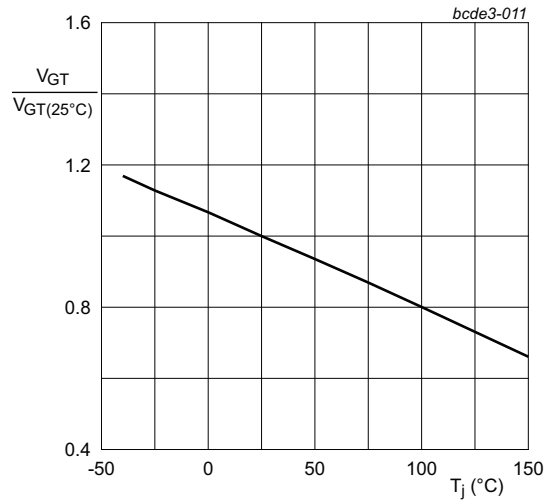


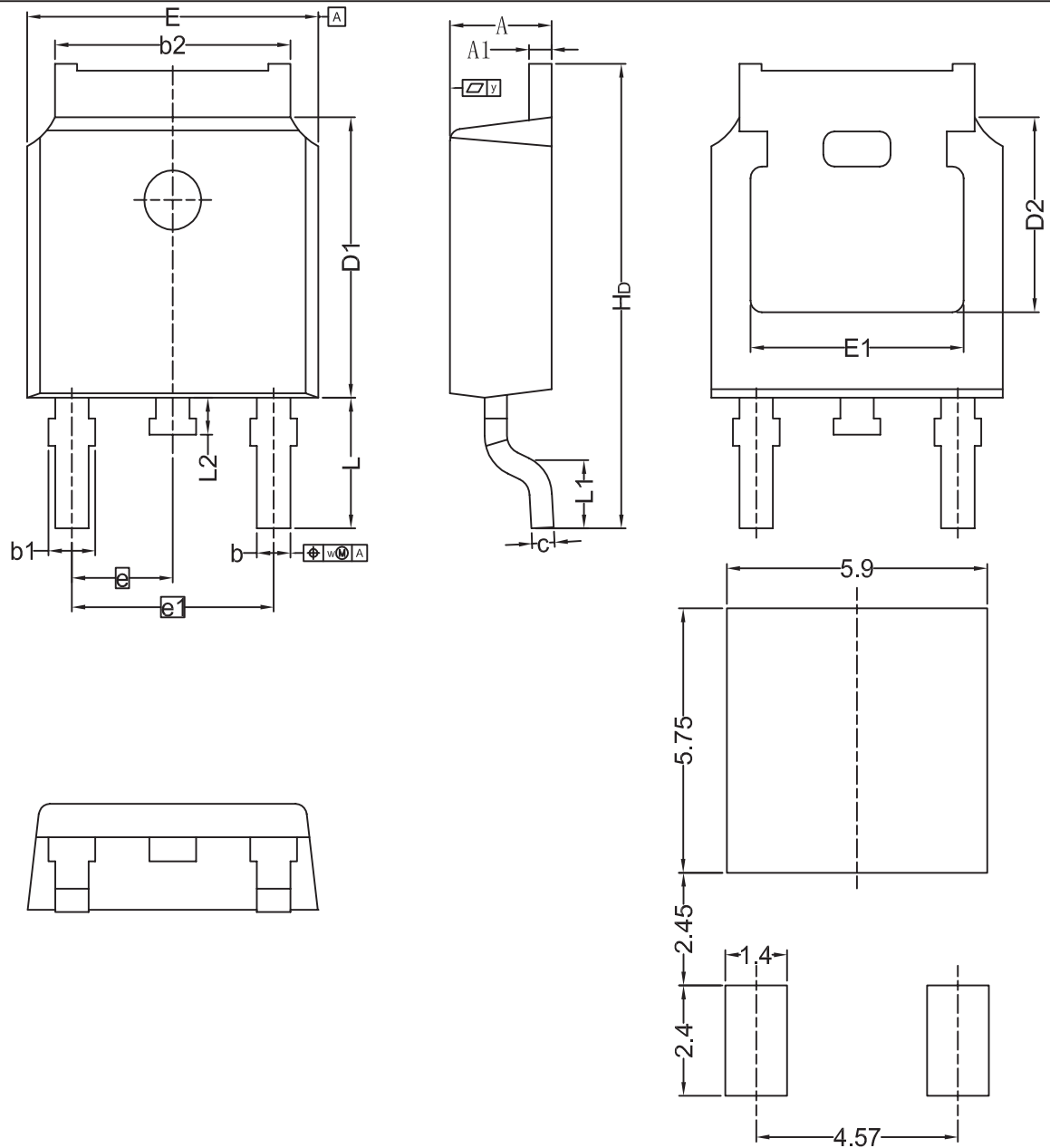
Fig. 11. Normalized gate trigger voltage as a function of junction temperature



### 11. Package outline

Plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)

TO252



Recommended Footprint

Unit	A	A1	b	b1	b2	c	D1	D2	E	E1	e	e1	H <sub>D</sub>	L	L1	L2	w	y
min	2.22	0.46	0.71	0.72	5.00	0.20	5.98	4.00	6.47	4.45	2.285	4.57	9.60	2.90 (Ref.)	0.50	0.50	0.20	
nom																		
max	2.38	0.93	0.89	1.10	5.46	0.56	6.22	---	6.73	---			10.40		---	0.90		0.20

## 12. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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- [2] The term 'short data sheet' is explained in section "Definitions".
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